

NCD30S10W

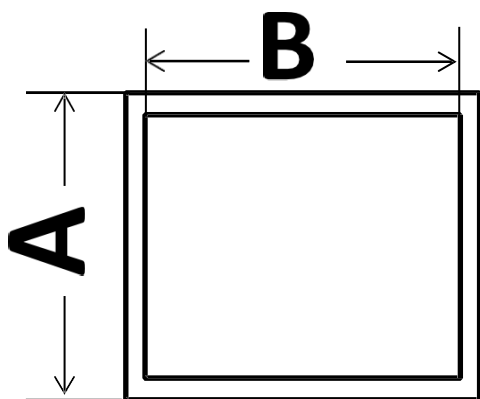
MOS-CONTROLLED RECTIFIER

Maximum Ratings(Per Leg) @T_A=25°C (unless otherwise specified)

Parameter	Symbol	Ratings	Units
Working Peak Reverse Voltage	V _{RWM}	300	V
Average Rectified Forward	I _{F(AV)}	10.0	A
Non-repetitive Peak Surge Current (8.3ms, half sine wave) Rated load (JEDEC METHOD)	I _{FSM}	150	A
Operating Junction Temperature	T _J	175	°C
Peak Repetitive Reverse Surge Current @2.0us, f=1KHz, T _J <175°C	I _{RRM}	2.5	A
Voltage Rate of Change	dv/dt	10	V/μS

Electrical Characteristics @T_A=25°C

Parameter	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Breakdown Voltage	V _{BR}	I _R = 250 μA	300	-	-	V
Forward Voltage Drop	V _F	I _F = 10 A	-	-	0.97	V
Reverse Leakage Current	I _R	T _A = 25°C, V _R = 300V	-	-	10	uA
		T _A =150°C, V _R =300 V	-	-	5	mA



Item	Information
Die Size (A)	1701 μm 1701 μm
Active Die Size (B)	1621 μm 1621 μm
Wafer Size	8"
Gross Die	9690
Top Metal	Al 5 μm
Back Metal	Ag
Scribe Line Width	40 μm
Wafer Thickness	200 μm